

N - CHANNEL ENHANCEMENT MODE FAST POWER MOS TRANSISTOR

TYPE	V _{DSS}	R _{DS(on)}	I _D
STH11NA50	500 V	< 0.6 Ω	11 A
STH11NA50FI	500 V	< 0.6 Ω	7 A

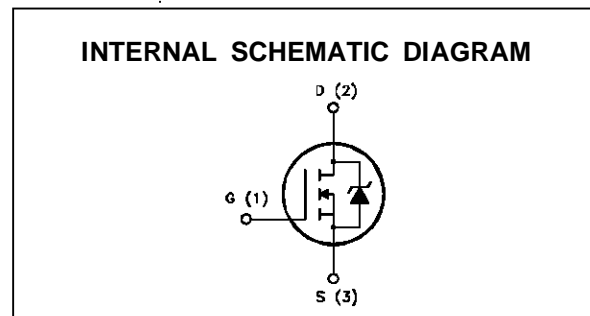
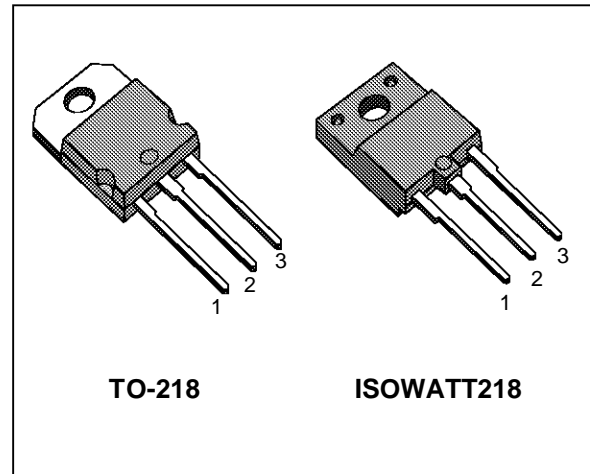
- TYPICAL R_{DS(on)} = 0.47 Ω
- ± 30V GATE TO SOURCE VOLTAGE RATING
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED
- REDUCED THRESHOLD VOLTAGE SPREAD

DESCRIPTION

This series of POWER MOSFETS represents the most advanced high voltage technology. The optimized cell layout coupled with a new proprietary edge termination concur to give the device low R_{DS(on)} and gate charge, unequalled ruggedness and superior switching performance.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STH11NA50	STH11NA50FI	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	500		V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	500		V
V _{GS}	Gate-source Voltage	± 30		V
I _D	Drain Current (continuous) at T _c = 25 °C	11	7	A
I _D	Drain Current (continuous) at T _c = 100 °C	6.9	4.4	A
I _{DM} (●)	Drain Current (pulsed)	44	44	A
P _{tot}	Total Dissipation at T _c = 25 °C	160	70	W
	Derating Factor	1.28	0.56	W/°C
V _{ISO}	Insulation Withstand Voltage (DC)	—	4000	V
T _{stg}	Storage Temperature	-65 to 150		°C
T _j	Max. Operating Junction Temperature	150		°C

(●) Pulse width limited by safe operating area

STH11NA50/FI

THERMAL DATA

		TO-218	ISOWATT218		
R _{thj-case}	Thermal Resistance Junction-case	Max	0.78	1.78	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	30		°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	0.1		°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max, δ < 1%)	11	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	600	mJ
E _{AR}	Repetitive Avalanche Energy (pulse width limited by T _j max, δ < 1%)	25	mJ
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (T _c = 100 °C, pulse width limited by T _j max, δ < 1%)	6.9	A

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	500			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating x 0.8 T _c = 125 °C			250 1000	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 30 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	2.25	3	3.75	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V I _D = 5.5 A V _{GS} = 10V I _D = 5.5 A T _c = 100°C		0.47	0.6 1.2	Ω Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} x R _{DS(on)max} V _{GS} = 10 V	11			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} x R _{DS(on)max} I _D = 5.5 A	6	9		S
C _{iss}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		1750	2500	pF
C _{oss}	Output Capacitance			250	370	pF
C _{rss}	Reverse Transfer Capacitance			80	130	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	$V_{DD} = 250\text{ V}$ $I_D = 5.5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3)		20 32	28 45	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 400\text{ V}$ $I_D = 11\text{ A}$ $R_G = 47\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		190		A/ μs
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 400\text{ V}$ $I_D = 11\text{ A}$ $V_{GS} = 10\text{ V}$		80 12 37	110	nC nC nC

SWITCHING OFF

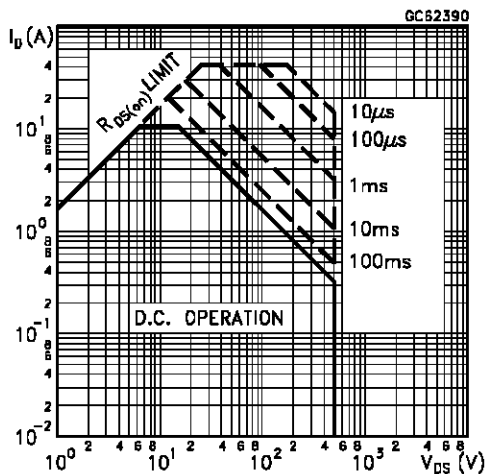
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 400\text{ V}$ $I_D = 11\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		16 12 30	22 18 42	ns ns ns

SOURCE DRAIN DIODE

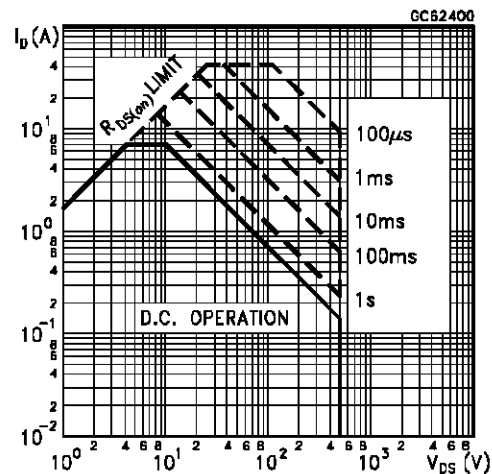
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}(\bullet)$	Source-drain Current Source-drain Current (pulsed)				11 44	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 11\text{ A}$ $V_{GS} = 0$			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 11\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		600 10.2 34		ns μC A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %
 (•) Pulse width limited by safe operating area

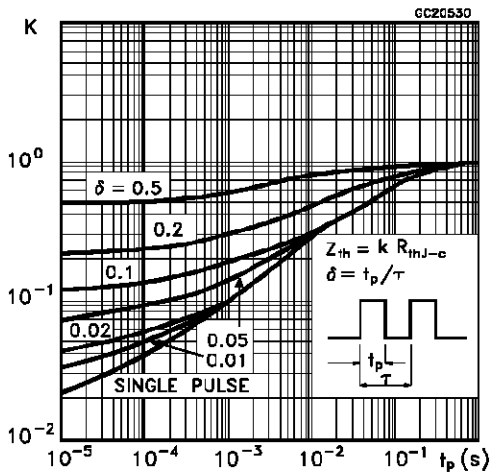
Safe Operating Areas for TO-218



Safe Operating Areas for ISOWATT218



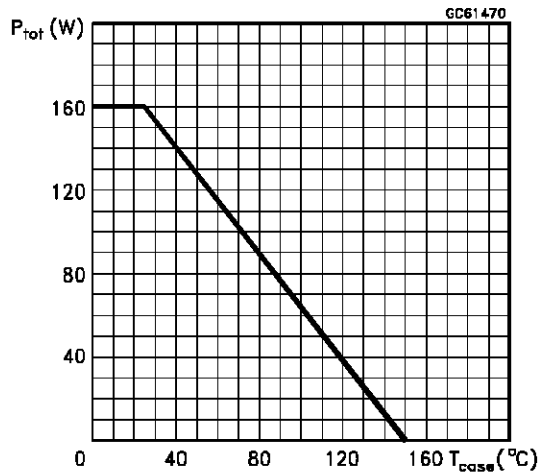
Thermal Impedance For TO-220



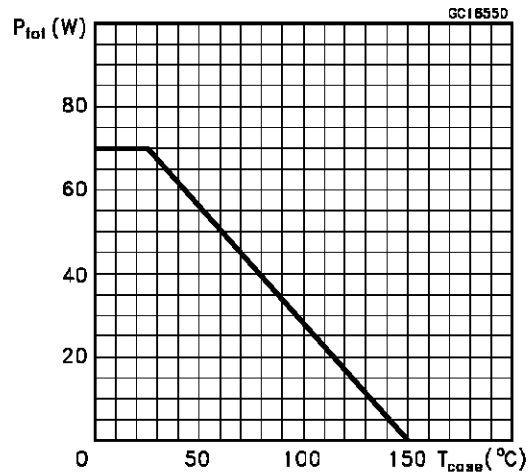
Thermal Impedance For ISOWATT220



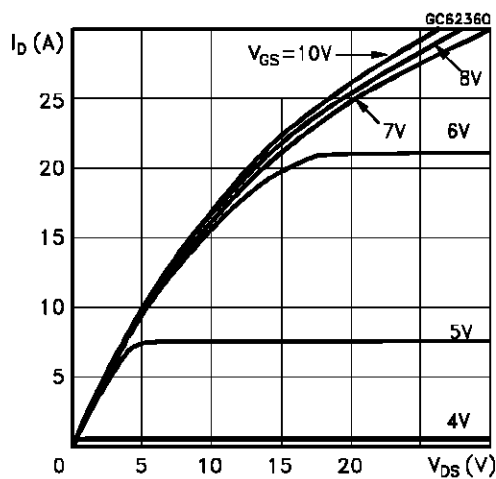
Derating Curve For TO-220



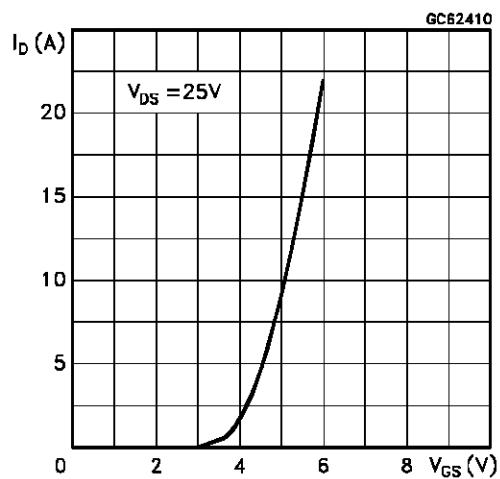
Derating Curve For ISOWATT220



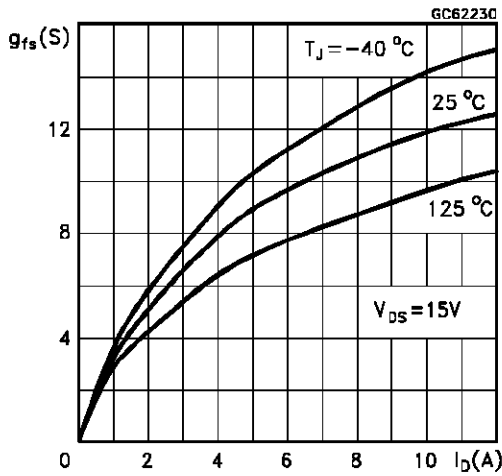
Output Characteristics



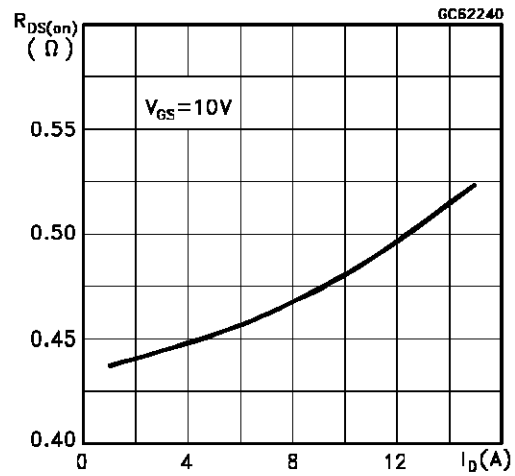
Transfer Characteristics



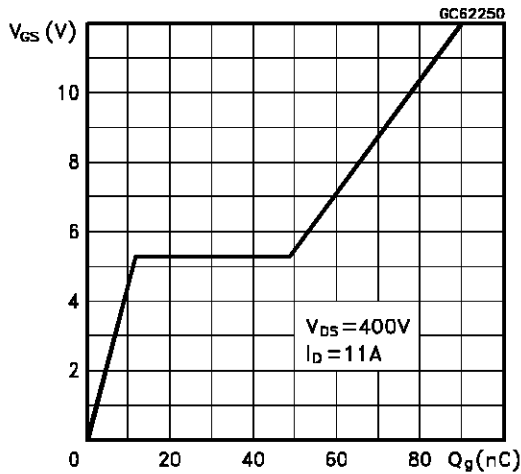
Transconductance



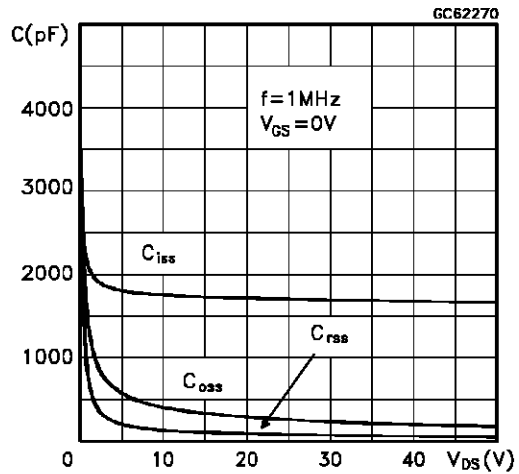
Static Drain-source On Resistance



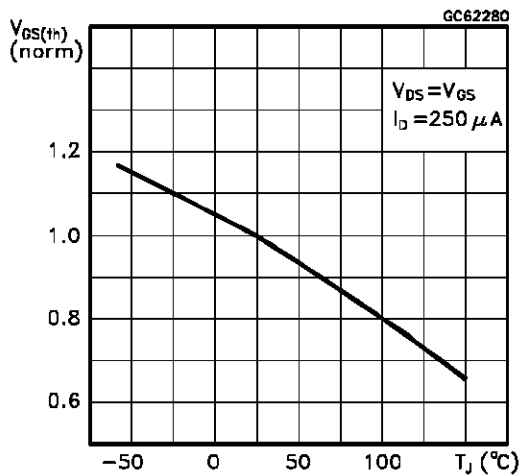
Gate Charge vs Gate-source Voltage



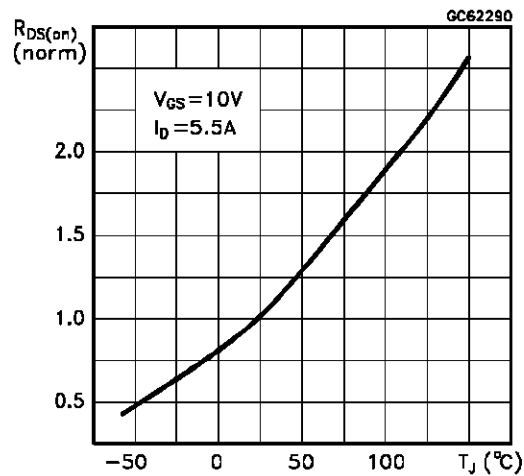
Capacitance Variations



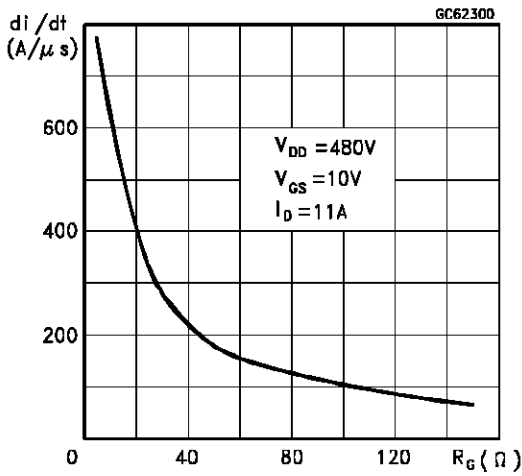
Normalized Gate Threshold Voltage vs Temperature



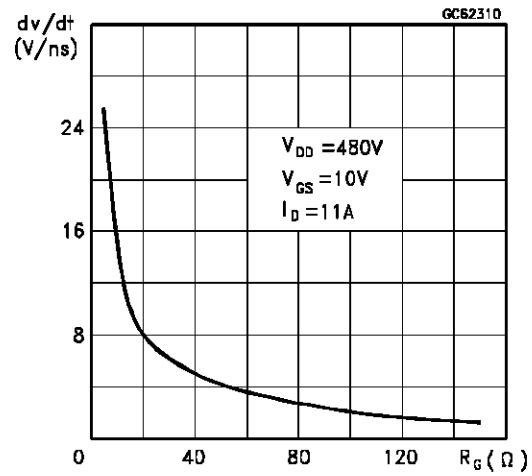
Normalized On Resistance vs Temperature



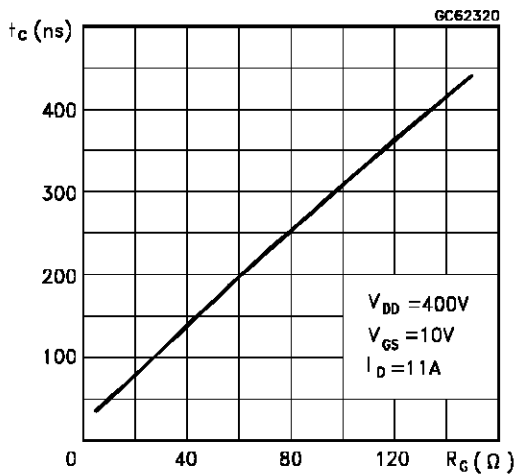
Turn-on Current Slope



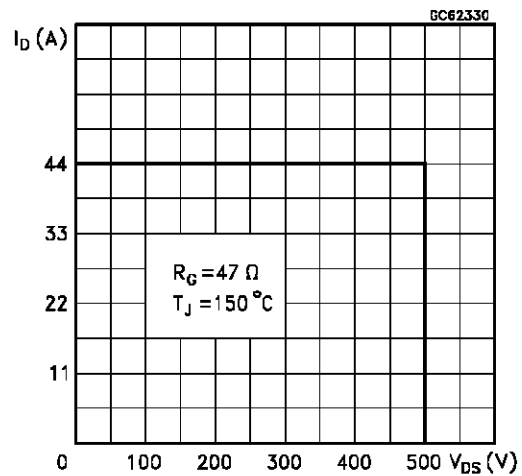
Turn-off Drain-source Voltage Slope



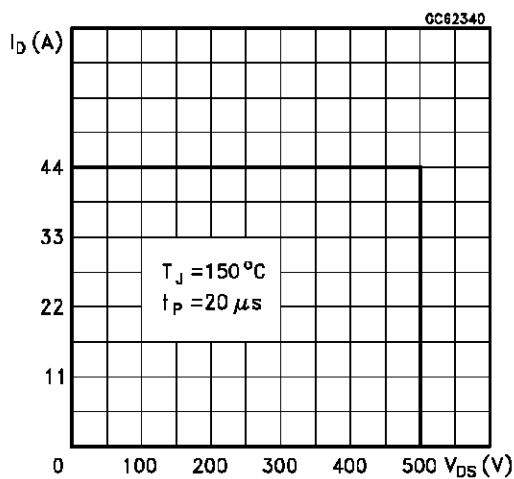
Cross-over Time



Switching Safe Operating Area



Accidental Overload Area



Source-drain Diode Forward Characteristics

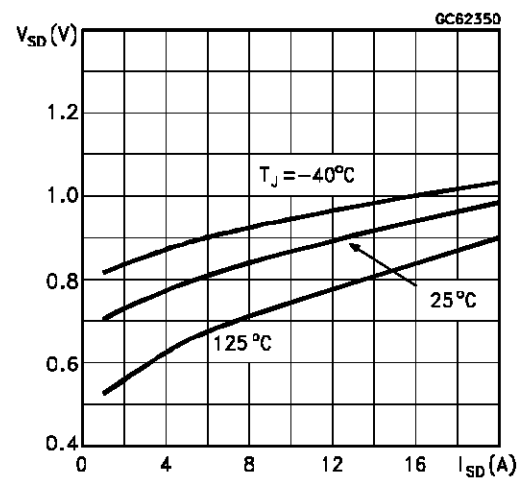


Fig. 1: Unclamped Inductive Load Test Circuits



Fig. 2: Unclamped Inductive Waveforms



Fig. 3: Switching Times Test Circuits For Resistive Load



Fig. 4: Gate Charge Test Circuit

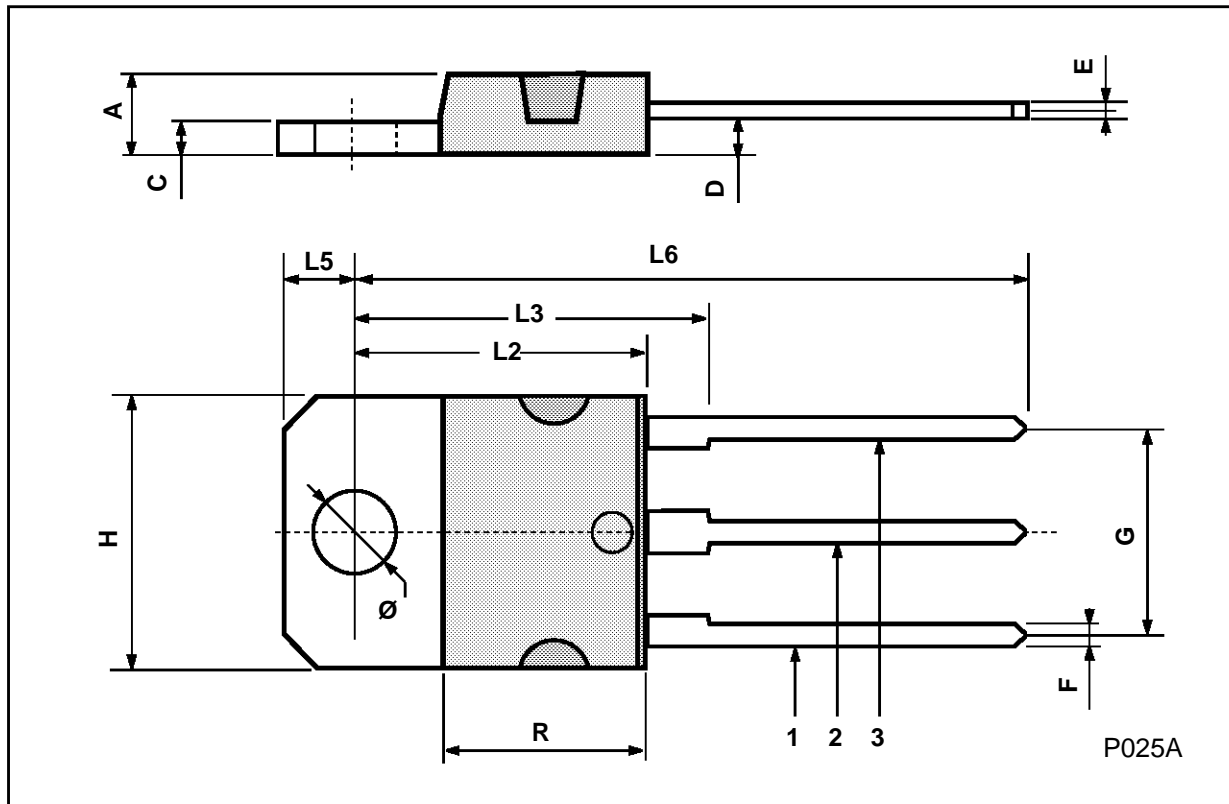


Fig. 5: Test Circuit For Inductive Load Switching And Diode Reverse Recovery Time



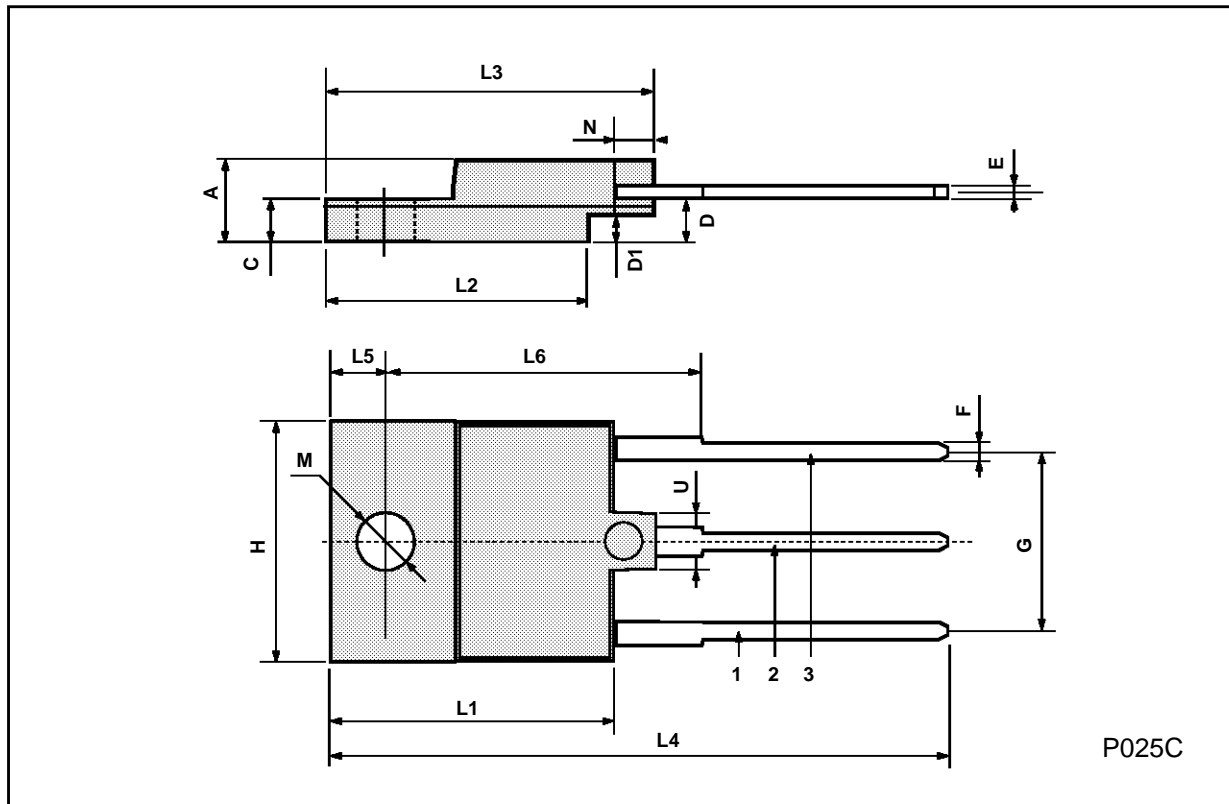
TO-218 (SOT-93) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		4.9	0.185		0.193
C	1.17		1.37	0.046		0.054
D		2.5			0.098	
E	0.5		0.78	0.019		0.030
F	1.1		1.3	0.043		0.051
G	10.8		11.1	0.425		0.437
H	14.7		15.2	0.578		0.598
L2	-		16.2	-		0.637
L3		18			0.708	
L5	3.95		4.15	0.155		0.163
L6		31			1.220	
R	-		12.2	-		0.480
Ø	4		4.1	0.157		0.161



ISOWATT218 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.210		0.222
C	3.3		3.8	0.130		0.149
D	2.9		3.1	0.114		0.122
D1	1.88		2.08	0.074		0.081
E	0.45		1	0.017		0.039
F	1.05		1.25	0.041		0.049
G	10.8		11.2	0.425		0.441
H	15.8		16.2	0.622		0.637
L1	20.8		21.2	0.818		0.834
L2	19.1		19.9	0.752		0.783
L3	22.8		23.6	0.897		0.929
L4	40.5		42.5	1.594		1.673
L5	4.85		5.25	0.190		0.206
L6	20.25		20.75	0.797		0.817
M	3.5		3.7	0.137		0.145
N	2.1		2.3	0.082		0.090
U		4.6			0.181	



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